

N-channel TrenchMOS standard level FET 11 September 2012

**Product data sheet** 

#### **Product profile** 1.

#### 1.1 General description

Standard level N-channel MOSFET in a SOT78 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

#### 1.2 Features and benefits

- AEC Q101 compliant •
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

#### **1.3 Applications**

- 12V, 24V and 48V Automotive systems
- Electric and electro-hydraulic power steering •
- Motors, lamps and solenoid control •
- Start-Stop micro-hybrid applications
- Transmission control •
- Ultra high performance power switching •

### 1.4 Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	100	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	-	120	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	349	W
Static char	acteristics	1		1			
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11		-	4.1	5.2	mΩ
Dynamic cl	haracteristics						
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 80 V; T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>		-	65	-	nC

#### Quick reference data Table 1

[1] Continuous current is limited by package.

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### 2. Pinning information

PinSymbol1G	Description		
1 G	•	Simplified outline	Graphic symbol
	gate	mb	D
2 D	drain	204	
3 S	source		G
mb D	mounting base; connected to drain	TO-220AB (SOT78A)	mbb076 S

# 3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK755R4-100E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A			

### 4. Marking

Table 4. Marking codes	
Type number	Marking code
BUK755R4-100E	BUK755R4-100E

### 5. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	100	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	100	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> = 175 °C; DC		-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	120	А
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>		-	112	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4		-	631	А

### **BUK755R4-100E**

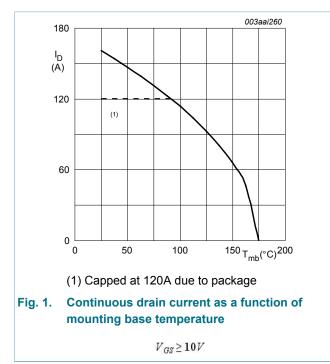
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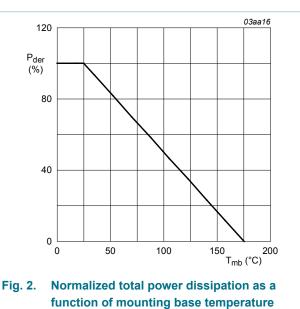
Symbol	Parameter	Conditions		Min	Мах	Unit
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	349	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					_
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	120	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	631	А
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 120 \text{ A};  \text{V}_{\text{sup}} \leq 100  \text{V};  \text{R}_{\text{GS}} = 50  \Omega; \\  \text{V}_{\text{GS}} &= 10  \text{V};  \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped}; \\ \hline \text{Fig. 3} \end{split}$	[ <u>2][3]</u>	-	387	mJ

Continuous current is limited by package. [1]

Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. Refer to application note AN10273 for further information. [2]

[3]

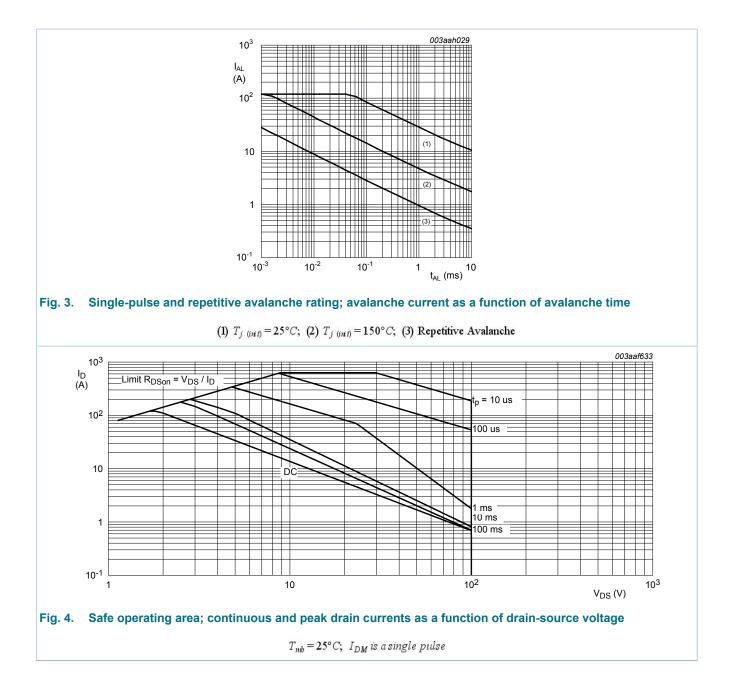




$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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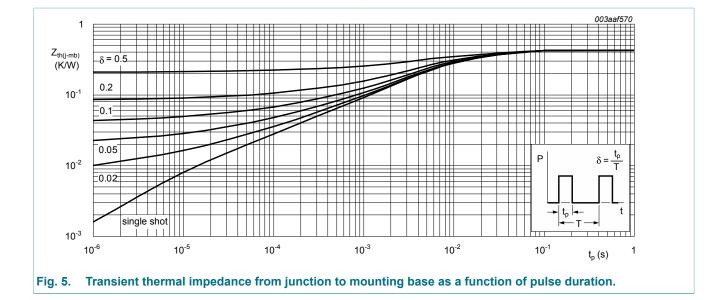


### 6. Thermal characteristics

Table 6. Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	-	0.43	K/W	
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	vertical in free air		-	60	-	K/W	

## BUK755R4-100E

#### N-channel TrenchMOS standard level FET



#### **Characteristics** 7.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	100	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	90	-	-	V
V <sub>GS(th)</sub> gate-source threshold voltage	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 9	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	4.5	V
I <sub>DSS</sub> drain leakage current	drain leakage current	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.15	2	μA
	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA	
I <sub>GSS</sub> gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA	
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	-	4.1	5.2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-	-	14	mΩ
Dynamic cł	naracteristics	· · ·	I			
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 25 A; $V_{DS}$ = 80 V; $V_{GS}$ = 10 V;	-	180	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13; Fig. 14</u>	-	34	-	nC
Q <sub>GD</sub>	gate-drain charge	1	-	65	-	nC

#### N-channel TrenchMOS standard level FET

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	8860	11810	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	770	925	pF
C <sub>rss</sub>	reverse transfer capacitance		-	546	750	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 80 V; R <sub>L</sub> = 3.2 Ω; V <sub>GS</sub> = 10 V;	-	37	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	62	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	158	-	ns
t <sub>f</sub>	fall time		-	80	-	ns
L <sub>D</sub> internal drain inductance	from upper edge of drain mounting base to centre of die	-	2.5	-	nH	
		from drain lead 6mm from package to centre of die	-	4.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bond pad	-	7.5	-	nH
Source-dra	in diode	· · ·				
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>	-	0.77	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{\rm S}$ = 20 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;	-	65	-	ns
Qr	recovered charge	V <sub>DS</sub> = 25 V	-	191	-	nC

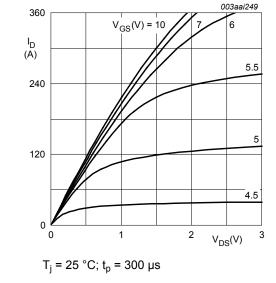


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

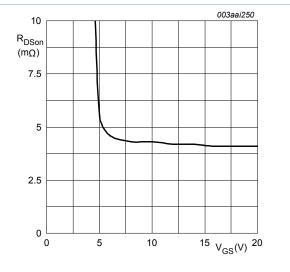
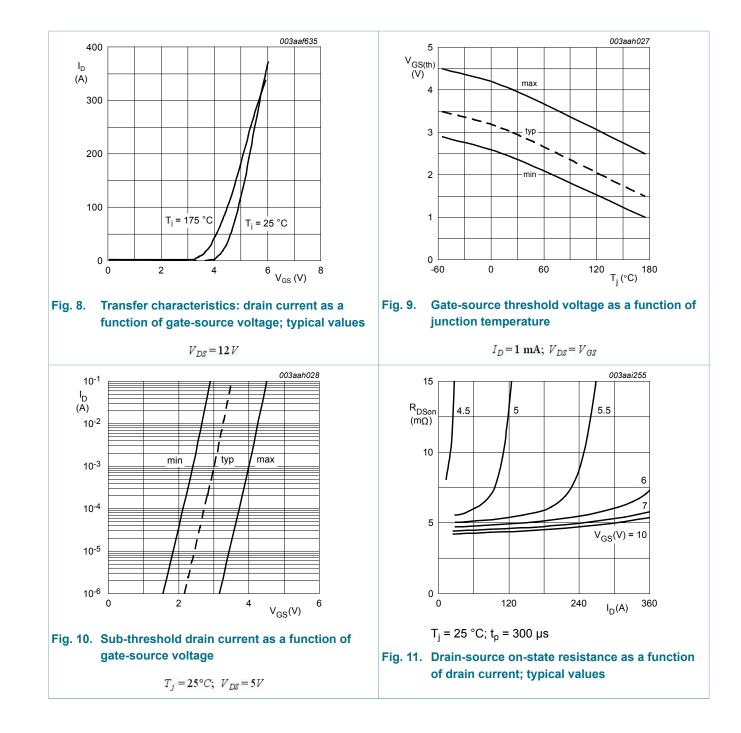


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 25A$ 

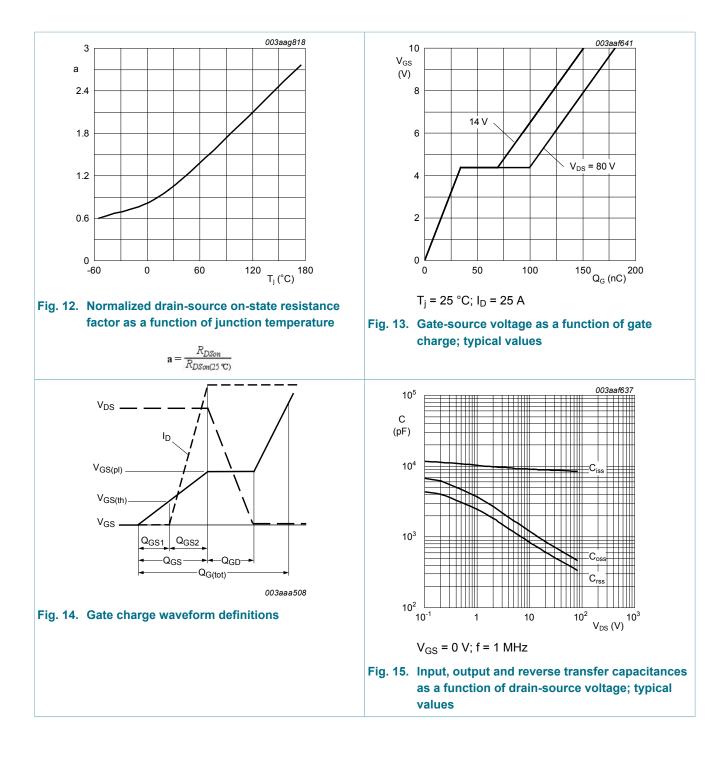
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#### N-channel TrenchMOS standard level FET



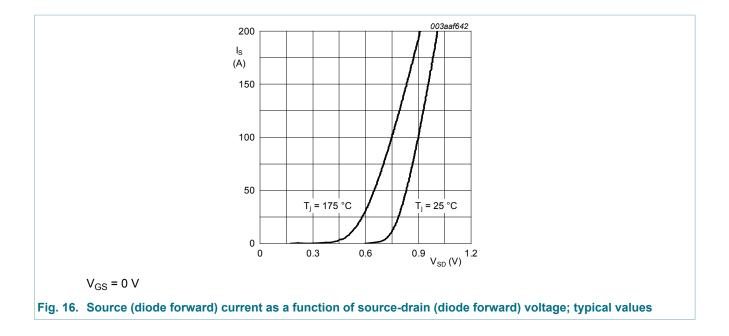
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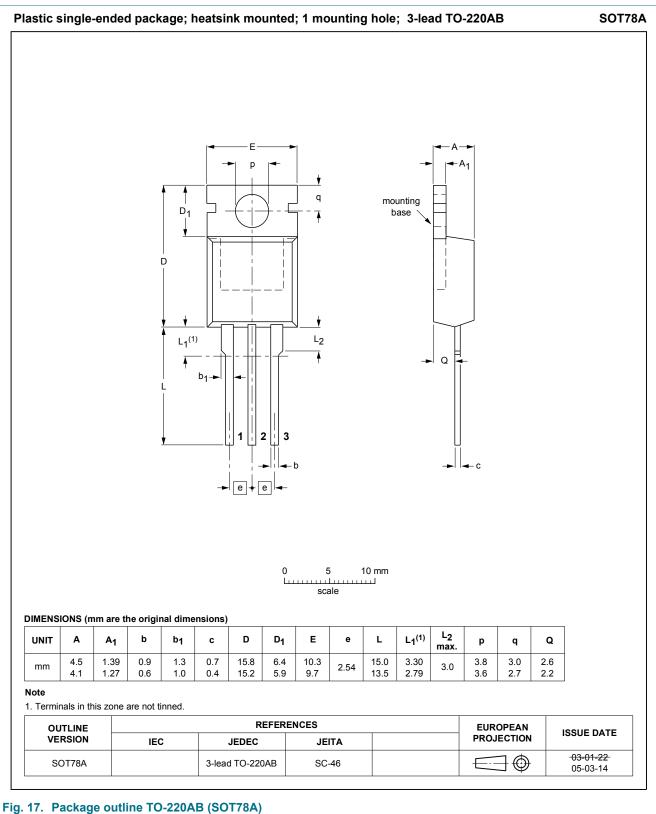
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### 8. Package outline



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#### 9. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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BUK755R4-100E

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#### N-channel TrenchMOS standard level FET

### **10. Contents**

Product profile	1
General description	1
Features and benefits	1
Applications	1
Quick reference data	1
Pinning information	2
Ordering information	2
Marking	2
Limiting values	2
Thermal characteristics	4
Characteristics	5
Package outline1	0
Legal information1	1
Data sheet status 1	1
Definitions1	1
Disclaimers1	1
Trademarks 12	2
	Product profile     General description       General description     Features and benefits       Applications     Quick reference data       Pinning information     Ordering information       Ordering information     Marking       Limiting values     Thermal characteristics       Characteristics     Package outline       Data sheet status     1       Definitions     1       Disclaimers     1       Trademarks     12

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